

Description

This device is especially designed to protect Subscriber Line Interface Circuit (SLIC) against transient overvoltage. Positive overloads are clipped with 2 diodes. Negative surges are suppressed by 2 Thyristors, their breakdown voltage being referenced to VBAT through the gate. This component presents a very low gate triggering current and minimizes overvoltage stress on the SLIC.

Feature

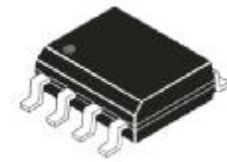
- | Dual programmable transient suppressor
- | Wide battery voltage supports
- | Low gate triggering current
- | High holding current
- | ESD Immunity(HBM): JESD22 Class 3B, $\geq 8\text{KV}$
- | MLS: Lever 1 - unlimited

Application

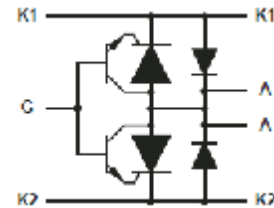
- | Switch Line Card
- | Access Network Line Card
- | PBX
- | VoIP

Pin Configuration

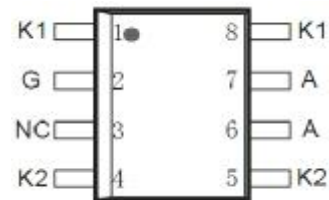
Pin #	Pin Name	Description
1, 4, 5, 8	K1, K2	Connect to subscriber lines (Tip/Ring)
2	G	Connect to battery (Reference Voltage)
6, 7	A	Connect ground
3	NC	Not connected



SOP-8



Schematic Diagram

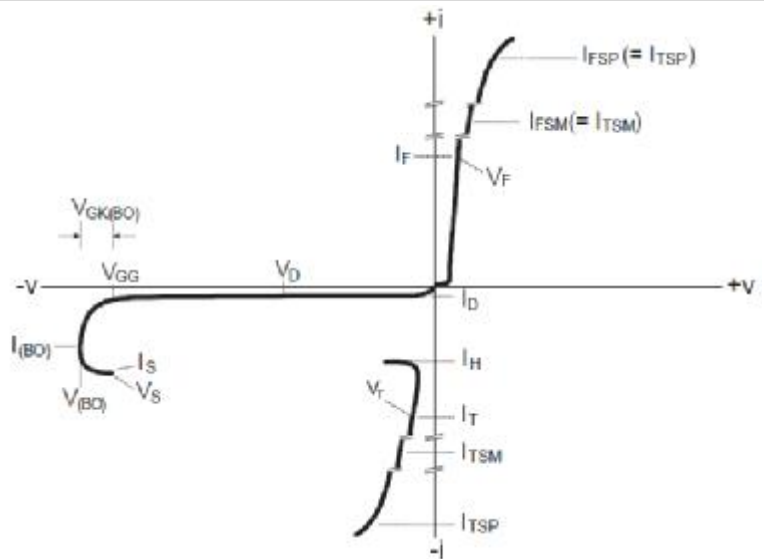


Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Non-repetitive peak on-state pulse current	I_{pp}	30	A
10/1000 μs		40	
5/310 μs		120	
2/10 μs			
Non repetitive surge peak on-state current (sinusoidal) 60Hz	I_{TSM}	6.5	A
0.5s		4.5	
1s		2.4	
5s		1.3	
30s		0.72	
900s			
Maximum voltage LINE/GROUND	V_{DRM}	-120	V
Maximum voltage GATE/LINE	V_{GKRM}	-120	V
Operating free-air temperature range	T_A	-40-85	$^{\circ}\text{C}$
Storage temperature range	T_{STG}	-40-150	$^{\circ}\text{C}$
Junction temperature	T_J	-40-150	$^{\circ}\text{C}$
Maximum lead temperature for soldering during 10s	T_L	260	$^{\circ}\text{C}$
Junction to free air thermal resistance	$R_{\theta JA}$	120	$^{\circ}\text{C/W}$

Electrical Characteristics ($T_A = 25^\circ\text{C}$)

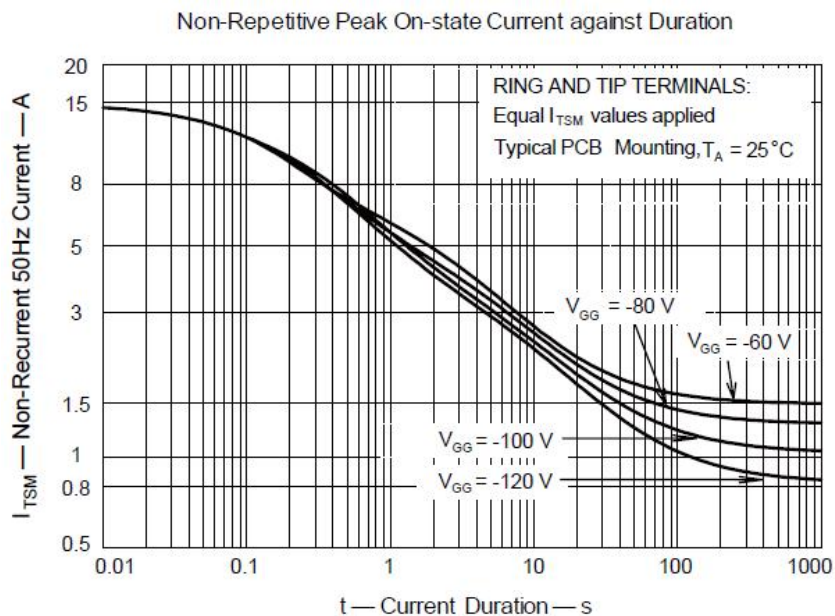
Parameter	Symbol
Off-state current	I_D
Holding current	I_H
Breakover voltage	$V_{(BO)}$
Forward voltage	V_F
Peak forward recovery voltage	V_{FRM}
Gate-cathode impulse breakover voltage	$V_{GK(BD)}$
Gate reverse current	I_{GKS}
Gate trigger current	I_{GT}
Gate-cathode trigger voltage	V_{GT}
Cathode-anode off-state capacitance	C_{KA}



Parameters Related to the Diode ($T_A = 25^\circ\text{C}$)

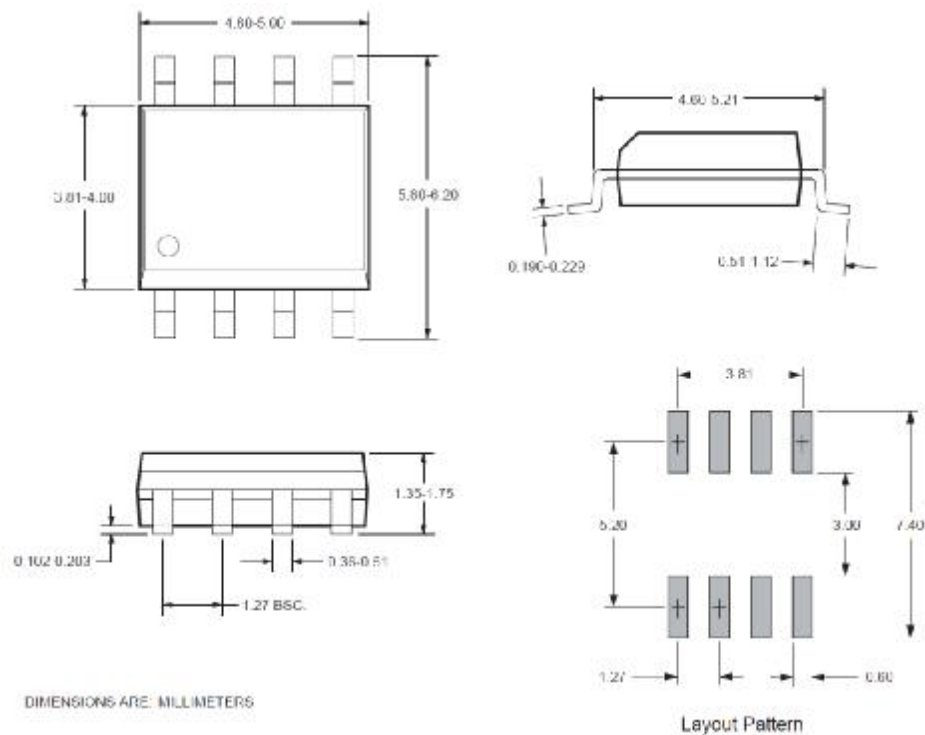
Symbol	Test Conditions	Min.	Typ.	Max.	Unit
V_F forward voltage	$I_F = 5\text{A}$, $t_w = 200\mu\text{s}$			3	V
V_{FRM} peak forward recovery voltage	$2/10\mu\text{s}$, $I_F = 100\text{A}$, $R_s = 50\Omega$, $di/dt = 80\text{A}/\mu\text{s}$			10	V

Parameters Related to the Thyristor ($T_A = 25^\circ\text{C}$)



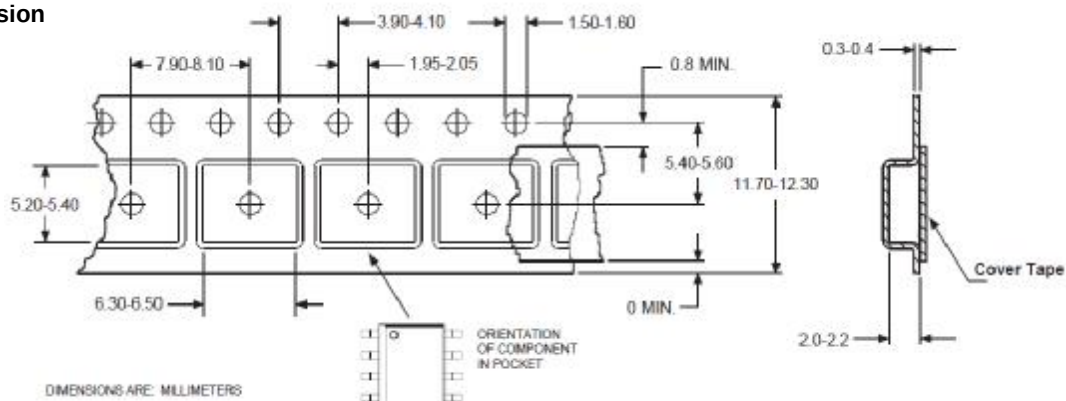
Symbol	Test Conditions	Min.	Typ.	Max.	Unit
I_D off-state current	$V_D=-170V, V_{GK}=0 \quad T_J=25^\circ C$			-5	μA
	$V_D=-170V, V_{GK}=0 \quad T_J=85^\circ C$			-50	μA
V_{BO} breakover voltage	$2/10\mu s, I_{TM}=100A, R_s=50\Omega, di/dt=-80A/\mu s, V_{GG}=-48V$			-60	V
I_H holding current	$I_T=-1A, di/dt=1A/ms, V_{GG}=-100V$	-150			mA
I_{GAS} gate reverse current	$V_{GG}=V_{GK}=-167V, V_{KA}=0 \quad T_J=25^\circ C$			-5	μA
	$V_{GG}=V_{GK}=-167V, V_{KA}=0 \quad T_J=85^\circ C$			-50	μA
I_{GT} gate trigger current	$I_T=3A, tp(g)\geq 20\mu s, V_{GG}=-100V$			5	mA
V_{GT} gate trigger voltage	$I_T=3A, tp(g)\geq 20\mu s, V_{GG}=-100V$			2.5	V
C_{AK} anode-cathode offstate capacitance	$f=1MHz, V_d=1V, I_G=0 \quad V_D=-3V$			110	pF
	$f=1MHz, V_d=1V, I_G=0 \quad V_D=-48V$			55	pF

Product Dimension

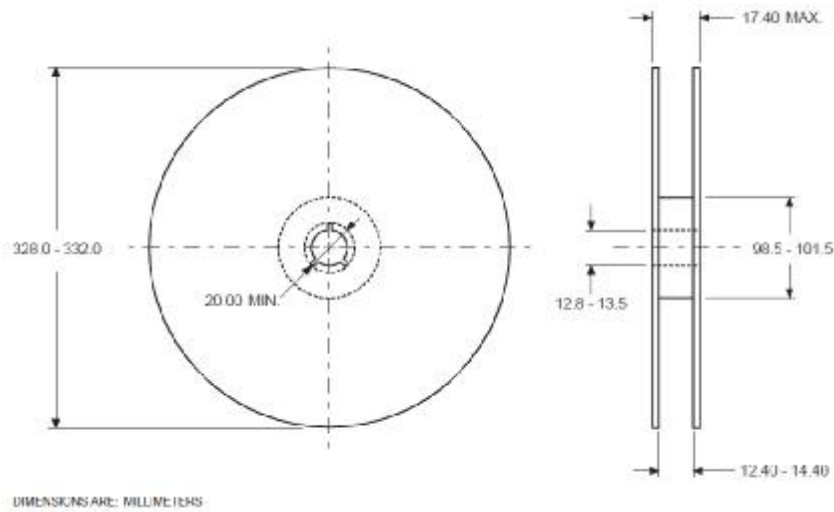


Package Information

Tape Dimension

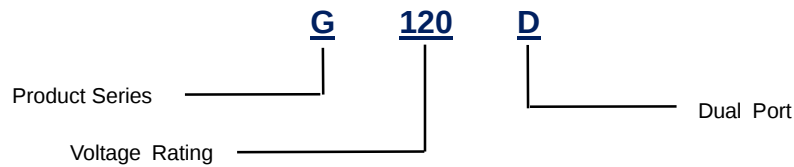


Reel Dimension



Marking and Order Information

Part Number System



Order Information

Device	Package	Net Weight	Carrier	Quantity	HSF Status
G120D	SOP-8	0.0080g	Tape & Reel	2,500pcs/reel	RoHS compliant

Marking



YYWW = Date Code

Specifications are subject to change without notice.

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